

**Enhancing the photoelectric performance of metal oxide semiconductors by  
introduction of dislocations**

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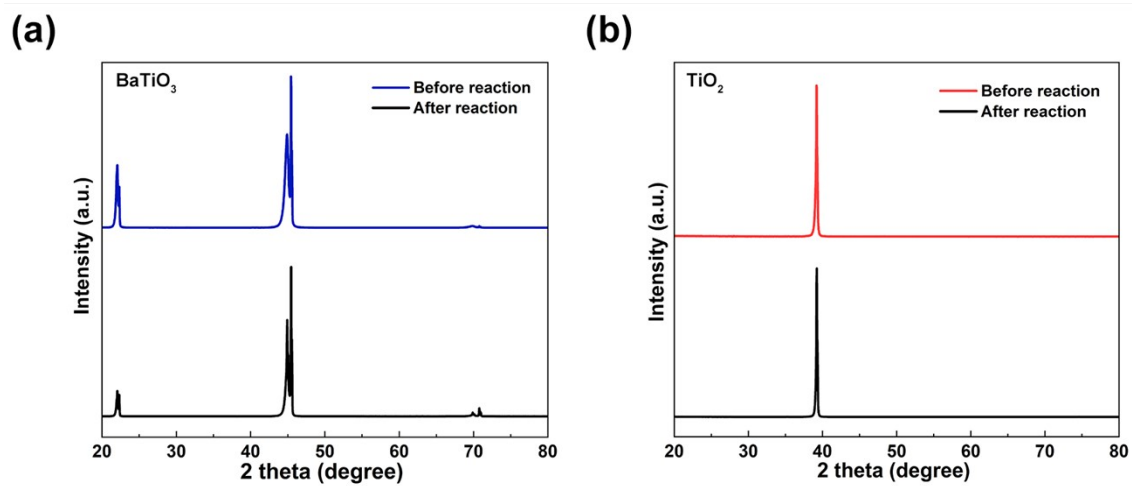


Figure S1. The XRD spectra comparison of a) BaTiO<sub>3</sub> (001) dislocation sample and b) TiO<sub>2</sub> (100) dislocation sample before and after reaction, respectively.

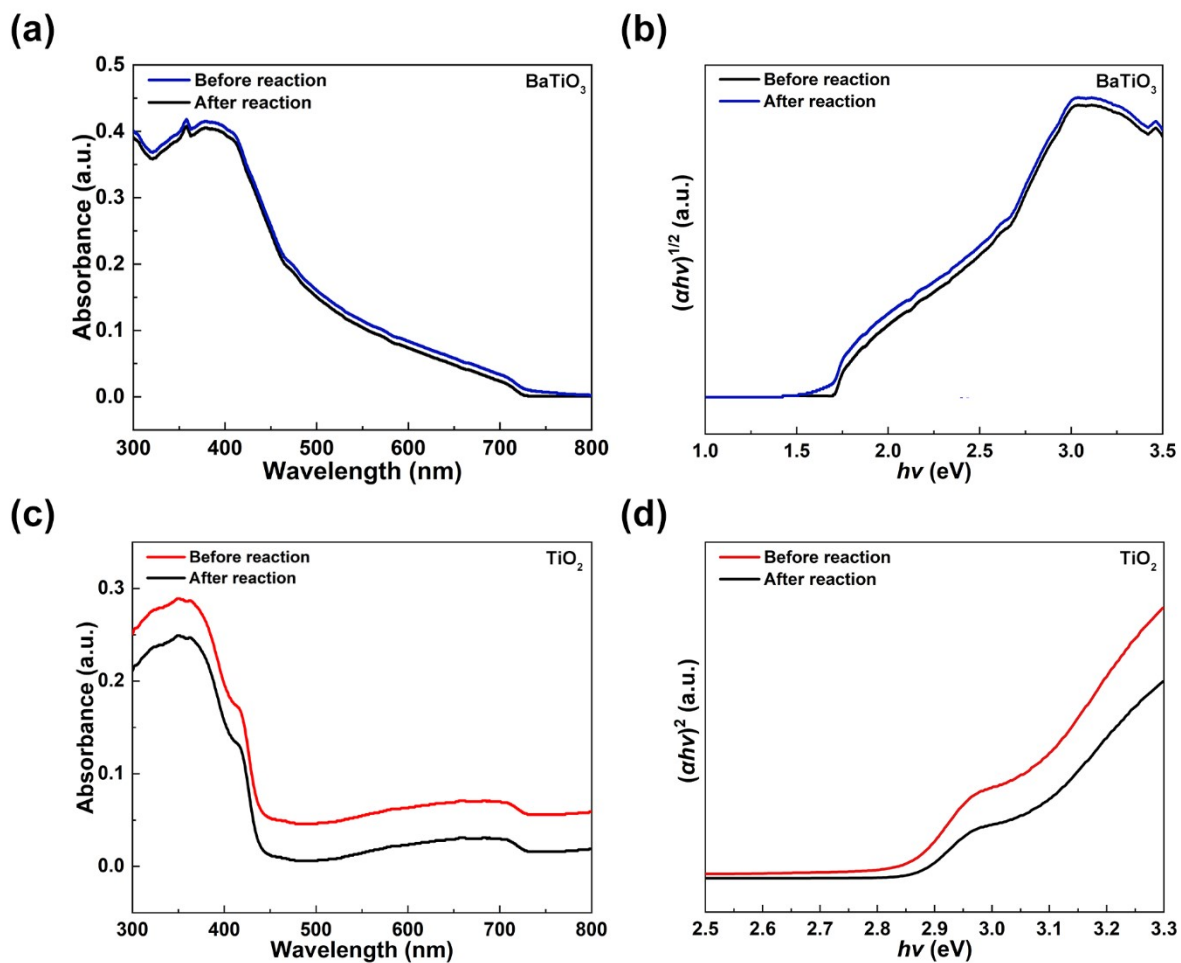


Figure S2. The UV-vis light absorbance spectra comparison of a) BaTiO<sub>3</sub> (001) dislocation sample and c) TiO<sub>2</sub> (100) dislocation sample and their corresponding bandgap Tauc plots of b) BaTiO<sub>3</sub> (001) dislocation sample and d) TiO<sub>2</sub> (100) dislocation sample before and after three consecutive runs, respectively.